NPN Epitaxial Planar Silicon Composite Transistors



CPH6519

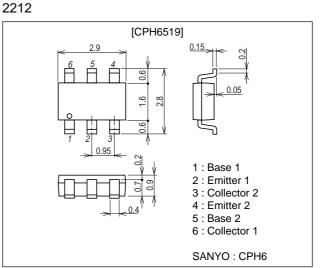
Low-Frequency General-Purpose **Amplifier, Driver Applications**

Features

- Composite type with 2 transistors contained in the CPH package currently in use, improving the mounting efficiency greatly.
- The CPH6519 is formed with two chips, being equivalent to the 2SC3689, placed in one package.
- · Adoption of FBET process.
- High DC current gain (hFE=800 to 3200).
- High VEBO (VEBO≥15V).
- Excellent in thermal equilibrium and pair capability.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|--------|------------|-------------|------|
| Collector-to-Base Voltage | VCBO | | 60 | V |
| Collector-to-Emitter Voltage | VCEO | | 50 | V |
| Emitter-to-Base Voltage | VEBO | | 15 | V |
| Collector Current | IC | | 100 | mA |
| Collector Current (Pulse) | ICP | | 200 | mA |
| Base Current | IB | | 20 | mA |
| Collector Dissipation | PC | 1unit | 350 | mW |
| Total Dissipation | Рт | | 500 | mW |
| Junction Temperature | Tj | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Electrical Characteristics at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|-------------------------------|----------------------|---|---------|------|--------------|------|
| | | | min | typ | max | Unit |
| Collector Cutoff Current | ICBO | V _{CB} =40V, I _E =0 | | | 0.1 | μΑ |
| Emitter Cutoff Current | IEBO | V _{EB} =10V, I _C =0 | | | 0.1 | μA |
| DC Current Gain | hFE | V _{CE} =5V, I _C =10mA | 800 | 1500 | 3200 | |
| DC Current Gain Ratio | hFE(small/ large) | VCE=5V, IC=10mA | 0.8 | 0.98 | | |
| Marking: 3F Continued on next | | | | | n next page. | |

Marking: 3F

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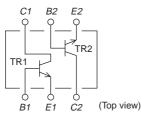
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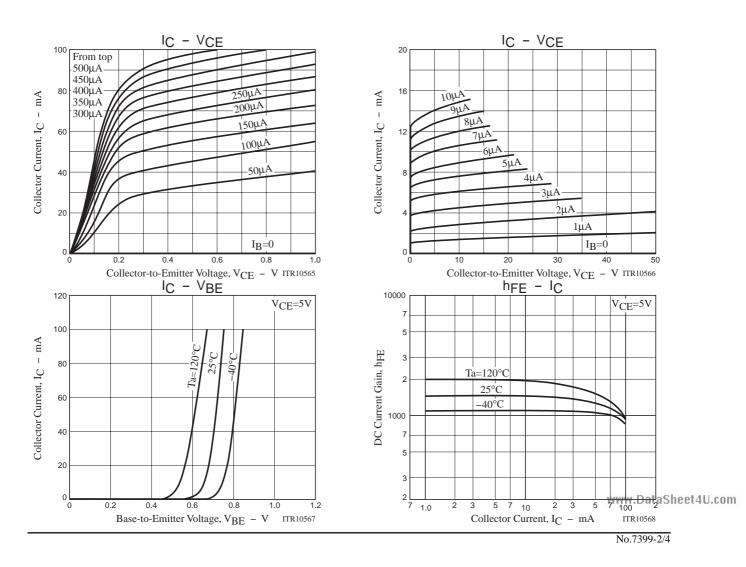
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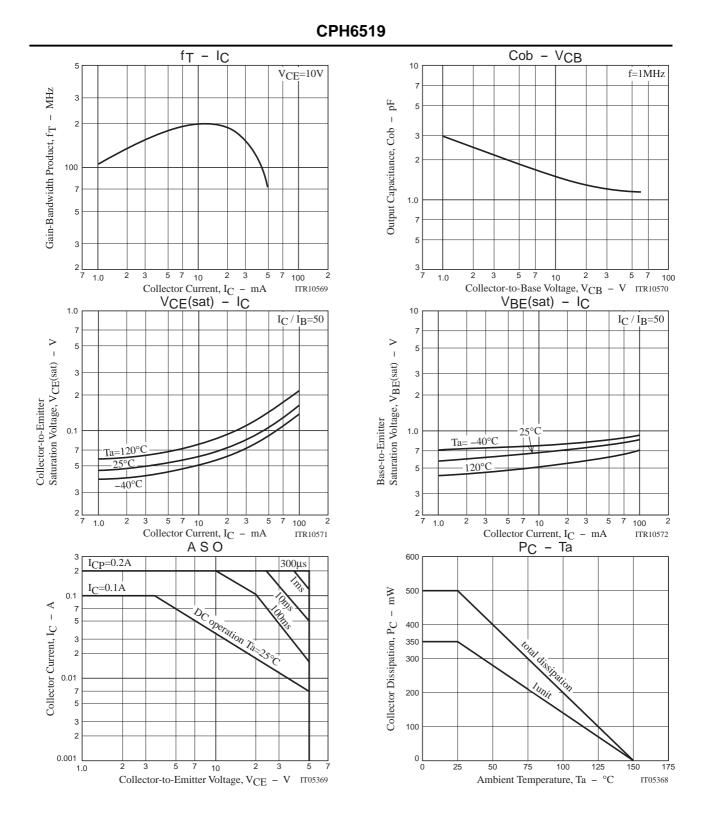
| Parameter | Symbol | Conditions | Ratings | | | 1.1-14 |
|---|-----------------------|--|---------|-----|-----|--------|
| | | | min | typ | max | Unit |
| Gain-Bandwidth Product | fT | V _{CE} =10V, I _C =10mA | | 200 | | MHz |
| Output Capacitance | Cob | V _{CB} =10V, f=1MHz | | 1.5 | | pF |
| Collector-to-Emitter Saturation Voltage | VCE(sat) | IC=50mA, IB=1mA | | 0.1 | 0.5 | V |
| Base-to-Emitter Saturation Voltage | V _{BE} (sat) | IC=50mA, IB=1mA | | 0.8 | 1.1 | V |
| Collector-to-Base Breakdown Voltage | V(BR)CBO | I _C =10μA, I _E =0 | 60 | | | V |
| Collector-to-Emitter Breakdown Voltage | V(BR)CEO | IC=1mA, RBE=∞ | 50 | | | V |
| Emitter-to-Base Breakdown Voltage | V(BR)EBO | I _E =10μA, I _C =0 | 15 | | | V |

Note : The specifications shown above are for each individual transistor.

Electrical Connection







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